

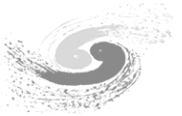
Some considerations on the CMOS sensors for CEPC MOST-2

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CEPC-MOST 2 Mini-workshop

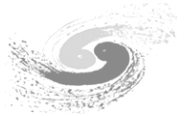
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Outline



- **General requirement**
 - Specifications
 - Chip architecture
- **Overall plan of the chip design**
- **Open questions and discussion**

First questions on motivations



- **What are we going to do?**
 - **To design a chip with full functionality, and to build a prototype ladder with several layers mounted**
 - **Very limited time**
 - **5 years in total, 3.5 years for the chip final design**
 - **Therefore:**
 - **It is very unlikely that we have parallel designs (not like MOST-1)**
 - **Have to be very focused on a unique chip design**
 - **Chip design tasks might be divided into blocks**
 - **The requirement, spec., interface of the chip have to be determined asap**
 - **Real design can be initiated asap to earn time**

General requirement- from CEPC MOST 1

- To achieve S.P. resolution
 - Digital pixel $\sim 16\mu\text{m}$
 - Analog pixel $\sim 20\mu\text{m}$ (power pulsing mode in ILC)
- To lower the material budget
 - Sensor thickness $\sim 50\mu\text{m}$
 - Heat load $< 50 \text{ mW/cm}^2$ constrained by air cooling
- To tackle beam-related background
 - $20\mu\text{s/frame?}$
 - 300krad/year & $3 \times 10^{12} \text{ neq/ (cm}^2 \cdot \text{year)?}$

Physics driven requirements

$\sigma_{s.p.}$ **2.8 μm**

Material budget **0.15% X_0/layer**

r of Inner most layer **16mm**

Running constraints

→ Air cooling

→ beam-related background

→ radiation damage

Sensor specifications

→ Small pixel **16 μm**

→ Thinning **50 μm**

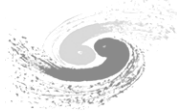
→ low power **50mW/cm²**

→ fast readout **20 $\mu\text{s?}$**

→ radiation tolerance

$\leq 1 \text{ Mrad/ year ?}$

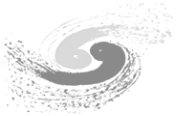
$\leq 1 \times 10^{12} \text{ neq/ (cm}^2 \text{ year) ?}$



Status of CEPC MOST-1

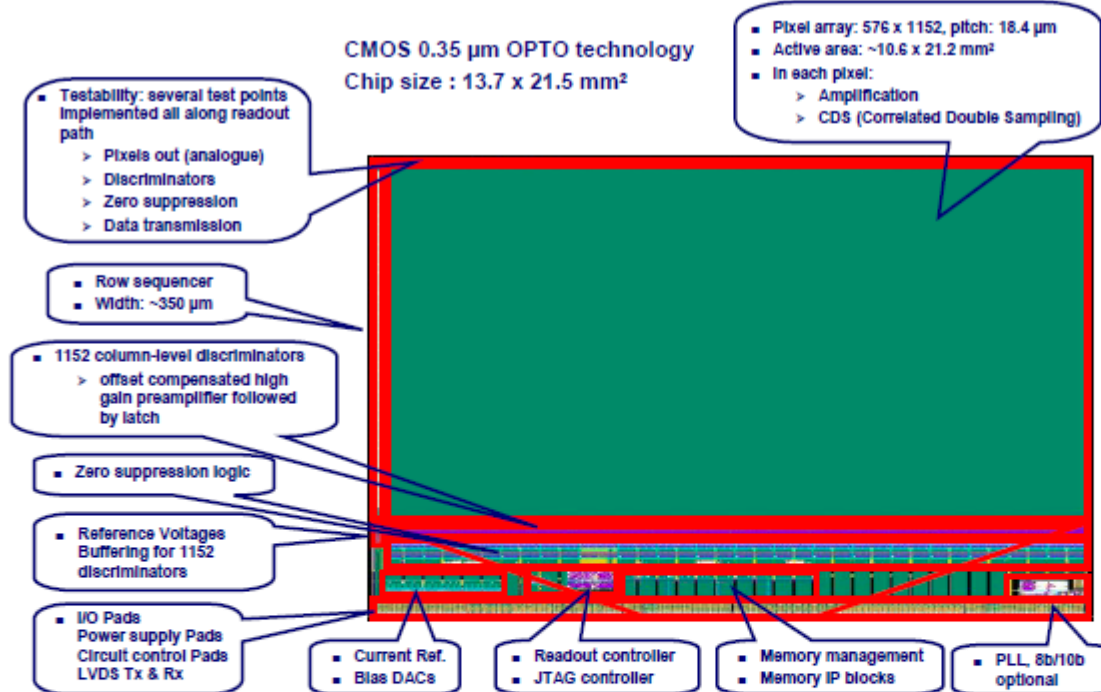
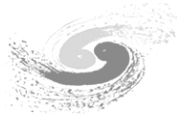
- **Initial sensor R&D targeting on**
 - Pixel pitch $\sim 16\ \mu\text{m}$
 - Power consumption $< 100\ \text{mW}/\text{cm}^2$
 - Integration time 10-100 μs
- **CPS design**
 - More focused, with major man power
 - All designs on Tower Jazz $0.18\ \mu\text{m}$ CIS process
 - sharing tapeout with CERN and IPHC
 - two versions of tapeouts
 - 1st ver.: only pixel sensors, analog readout
 - 2nd ver.: in-pixel digitization, parallel design on readout scheme
 - rolling shutter readout (IHEP) $22\ \mu\text{m} \times 22\ \mu\text{m}$ / async. readout (CCNU) $25\ \mu\text{m} \times 25\ \mu\text{m}$
 - Chip periphery: voltage DACs, readout logic, analog chain
- **SOI design**
 - Develop in-pixel circuit for minimum layout area
 - SOI-collaboration between IHEP & KEK
 - Two ver. of tapeouts: $16\ \mu\text{m} \times 16\ \mu\text{m}$ in-pixel discrimination

Experiences and comments from CEPC MOST-1



- **Pixel size**
 - Aiming for $16\mu\text{m} \times 16\mu\text{m}$, however very challenging in the current process (not even reported worldwide)
 - Achieved in the SOI efforts, but very little room left for any more func.
- **Readout time**
 - Aiming for a fast readout $< 10\mu\text{s}$, final goal $1\mu\text{s}$?
 - Also very challenging under the power consumption constraints
- **Power: aiming for $50\text{mW}/\text{cm}^2$ as the final goal**
 - Less periphery block integrated (some are hot elements: LDO/ Interface)
 - A brief evaluation: not achieved so far
- **Wafer thinning**
 - Not possible so far (MPW and sharing tapeout)
- **Simulation consistency**
 - Still needs careful test to prove
- **Comments and questions**
 - **To meet the final goal for CEPC is really challenging**
 - **No prior success of the similar chips worldwide**
 - most of them are done by more experienced engineers than us
 - Should we really be so aggressive on specs? Or maybe we should be conservative because we need to build a real ladder in very limited time

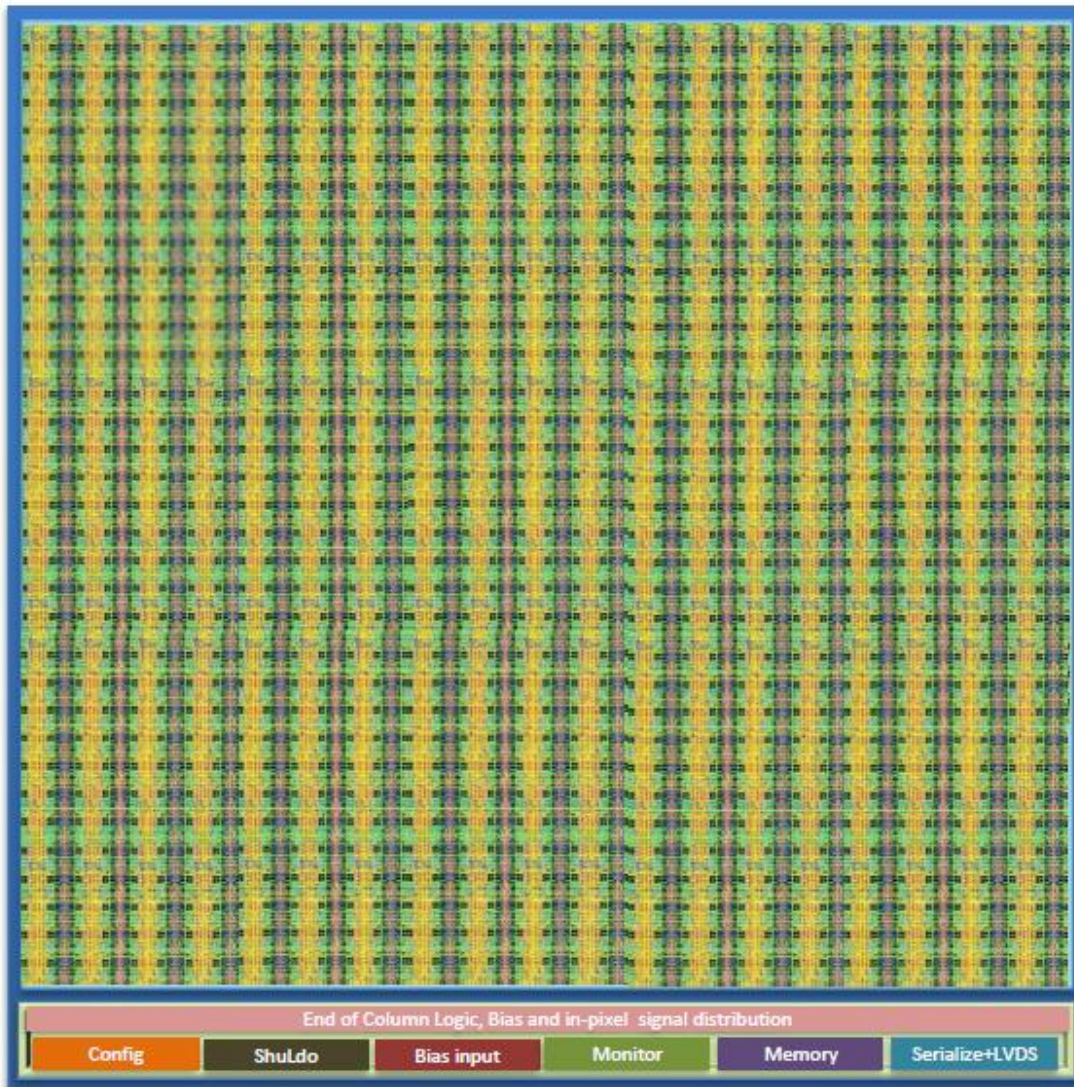
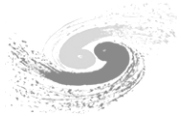
MIMOSA-26 chip architecture



Main characteristics of MIMOSA26 sensor equipping EUDET BT:

- Column // architecture with in-pixel Amp & CDS and end-of-col. discrimination, followed by \emptyset
- Active area: $21.2 \times 10.6 \text{ mm}^2$, 1152 x 576 pixels, pitch: 18.4 μm $\rightarrow \sigma_{\text{sp.}} < \sim 4 \mu\text{m}$
- Read out time $< \sim 100 \mu\text{s}$ (10^4 frames/s) \rightarrow suited to $> 10^6$ particles/cm²/s
- Yield $\sim 90\%$ (75% fully functional sensors thinned to 120 μm + 15% (showing one bad row or column)
- Thinning yield to 50 μm $\sim 90\%$

ATLAS CMOS-1 Sensor Overview



Active Matrix

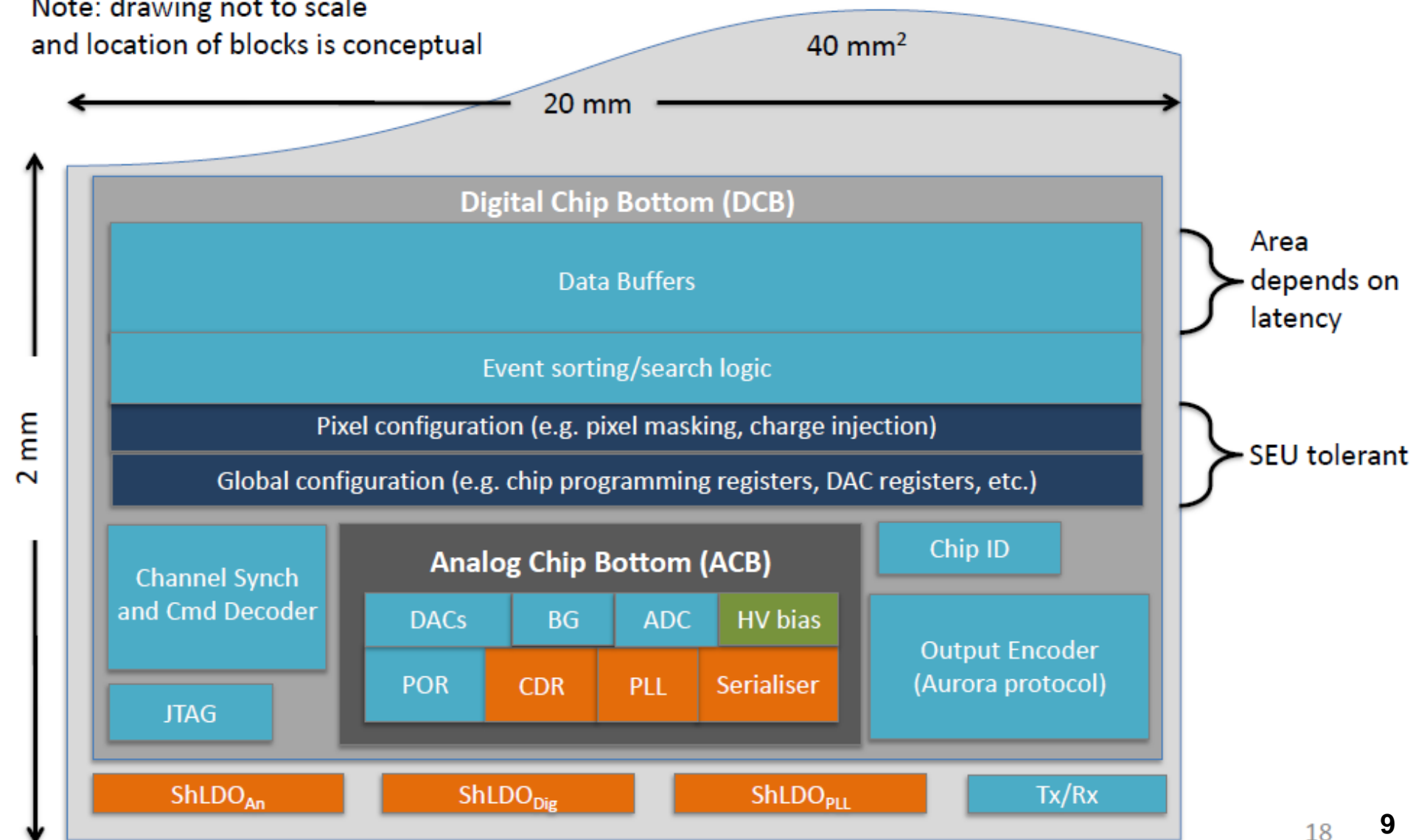
- Active area 19.2 x 20 mm²
- Each pixel contains CSA + discriminator + buffer
- Readout in double column structure either synchronously or asynchronously

Periphery

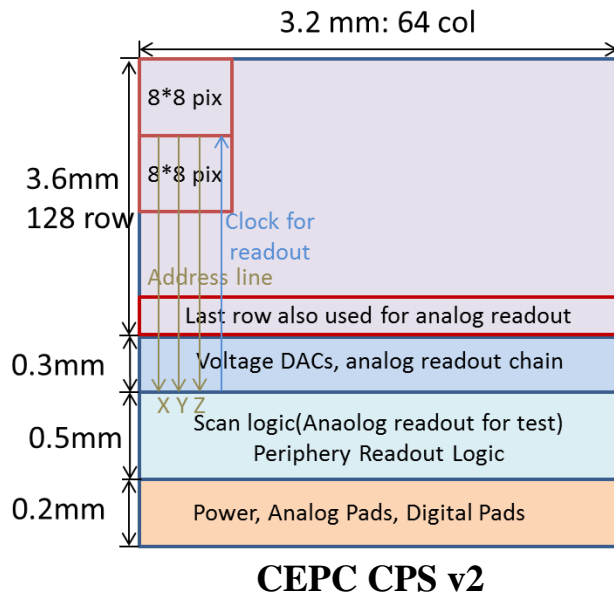
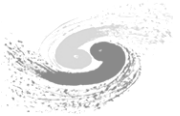
- End of Column Logic
- Common blocks to interface to ITk

Common Periphery Block Diagram (based heavily on RD53A)

Note: drawing not to scale
and location of blocks is conceptual



Chip overall architecture – CEPC MOST-1



- Compared with the exist chips, it seems that we have almost full func. in pixels
- Current chip only integrates basic periphery blocks and basic logics
- Q: do we need more complex readout logic
 - Depends on event rate, occupancy, and bunch crossing structure
 - If high, we probably need on chip RAM and some level of trigger
- Q: do we need other commonly used blocks: LDO, PLL
 - Very likely
 - Otherwise system design less compact: on-board components
 - Material budget issues
 - On-board component tends to be less rad-hard than on-chip rad-hard design

Consideration of the CEPC MOST-2 sensor

- **A chip aiming for prototype + full funcs. + time is short !**
- **1st: Specs. need to be fixed**
 - Better do not be too optimistic
- **Borrow the experience and designs from MOST-1**
 - Especially the pixel design
 - But it better that the pixel size be further shrinked
- **Should we try other processes?**
 - **TJ 0.18 μ m:**
 - existed experience, but pixel size limits already reached
 - Has to coordinate the tapeout schedule with collaborators– not good for a time limit project
 - **XX 0.15 μ m or even less?**
 - Might gain benefit to shrink the pixel size
 - **Can we try to establish dedicated collaboration with foundries?**
 - May get dedicated process that is optimized for CPS (even rad-hard?)
 - Possible to know more “secret” of the process– esp. important for sensor design
 - Might have free offers of tapeout
 - **Q: do we know any proof of the rad-hardness of a new process?**
 - When design initiates, it is very unlikely to change the process

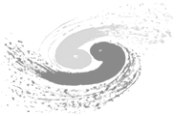
Consideration of the CEPC MOST-2 sensor

- **Pixel chip=pixel array($\sqrt{?}$) + periphery**
- **Carefully think about the overall chip functionality, especially the consideration for a real prototype**
- **How the chip works?**
 - **How the pixel level data are processed?**
 - **Zero-suppression? On-chip FIFO?**
 - **Not clear, need to be decided**
 - **How the chip is readout?**
 - **A BESIII-ladder like readout?**
 - **Signals of multiple chips all routed on PCB to the edge**
 - **Quite a experience learned from BESIII**
 - **Daisy-chain readout?**
 - **Based on high speed serial link; less reliable**
 - **Or even design a dedicated “Module Controller Chip (MCC)” like ATLAS?**
 - **My comments: less likely due to the limited time**
 - **My comments: a BESIII-like readout may still be the most possible solution**

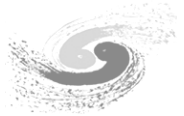
Consideration of the CEPC MOST-2 sensor

- **How we divide the design tasks among collaborators?**
 - **We will design a real prototype in very limited time, so better deliver the tasks to the collaborators with experiences on that part**
 - **Less R&D, more engineering**
 - **Chip overall design and simulation**
 - **Pixel array – better based on MOST-1**
 - **Sensor re-simulation**
 - **Pixel optimization**
 - **Column readout**
 - **Periphery Digital Pre-processing– new but somewhat independent**
 - **Functionality TBD**
 - **Common blocks in periphery – rad-hard!**
 - **Pixel array configuration (✓)**
 - **PLL (existed experience)**
 - **LDO (???any report in Chinese HEP society?)**
 - **Bandgap+Bias DAC (✓)**
 - **Serializer + Tx/Rx (✓)**
 - **Other common blocks: JTAG, decoder**

General schedule of the chip development



- **Scheduled in 3.5y till final tapeout My worries:**
 - 2~3 MPW tapeouts, 1~2 full mask tapeout expected
- **-0.5~0y**
 - Can we decide the process?
- **0~0.5y**
 - Specifications determined
 - Pixel size, readout speed, power
 - Key interface of the chip decided
 - Sync or async readout, HV, Tx/Rx to PCB...
 - Design tasks devided and delivered
- **0.5~1.3y: 1st MPW tapeout**
 - Full func. digital pixel in medium pixel array
 - Basic periphery blocks integrated
 - New blocks tapeout and evacuated separately
- **1.3~1.9y: 2nd MPW tapeout**
 - Test of the 1st chip (3month)
 - Full funcationalily chip in medium pixel array
- **1.9~2.5y:**
 - Test of the 2nd chip (2month)
 - Modified 3rd MPW or 1st full mask
- **2.5~3.1y:**
 - Test of chip (3m for MPW/6m for full mask)
 - DAQ debug and ladder debug
- **3.1~3.5y:**
 - Final tapeout



- **My worries:**
 - **We really need more system level electronic designers**
 - No man power for the chip test (from the name list)
 - The test setup has to be designed before hand and ready in time
 - Heavy job in chip test
 - Not easy from chip to DAQ, also need experiences on mechanical design
 - Time is really short, both for chip design and ladder design
 - Parallel tasks in the project schedule is great, but might be to optimistic: ladder design usually waits for the final chip
 - Also very challenging for the chip handling when thinned to 50μm
- **Very limited considerations were proposed**
 - Let's discuss